

1N6792
1N6792R

Features

- Tungsten/Platinum schottky barrier for very low VF
- Oxide passivated structure for very low leakage currents
- Guard ring protection for increased reverse energy capability
- Epitaxial structure minimizes forward voltage drop
- Hermetically sealed, low profile ceramic surface mount power package
- Low package inductance
- Very low thermal resistance
- Available as standard polarity (strap-to-anode, 1N6792) and reverse polarity (strap-to-cathode: 1N6792R)

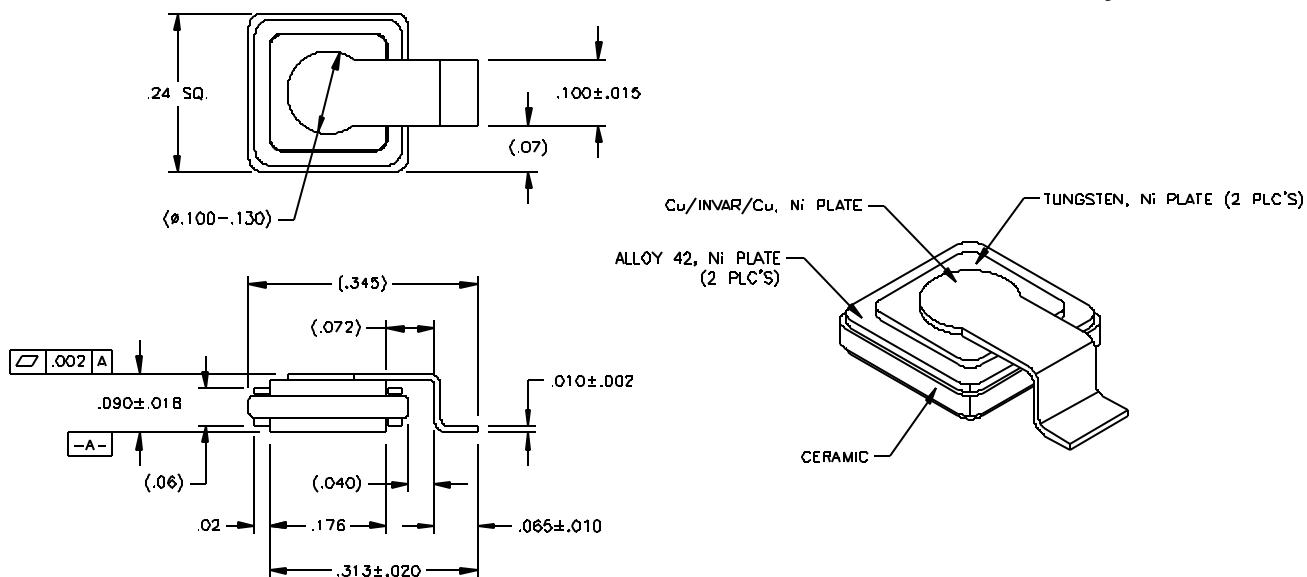
45 Volts
25 Amps

**LOW VOLTAGE
 DROP SCHOTTKY
 DIODE**

Maximum Ratings @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	MAX.	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	45	Volts
Working Peak Reverse Voltage	V_{RWM}	45	Volts
DC Blocking Voltage	V_R	45	Volts
Average Rectified Forward Current, $T_c \leq 145^\circ C$	$I_{F(ave)}$	25	Amps
derating, forward current, $T_c \geq 145^\circ C$	dI_F/dT	(3.3)	Amps/ $^\circ C$
Nonrepetitive Peak Surge Current, $t_p = 8.3$ ms, half-sinewave	I_{FSM}	125	Amps
Peak Repetitive Reverse Surge Current, $t_p = 1\mu s$, $f = 1\text{kHz}$	I_{RRM}	2	Amp
Junction Temperature Range	T_j	-65 to +175	$^\circ C$
Storage Temperature Range	T_{stg}	-65 to +175	$^\circ C$
Thermal Resistance, Junction to Case: 1N6792 1N6792R	θ_{JC}	1.25 tbd	$^\circ C/W$

Mechanical Outline ThinKey™2



1N6792**1N6792R****Microsemi**
Santa Ana, CA
Programmable Power by Technology

Electrical Parameters

DESCRIPTION	SYMBOL	CONDITIONS	MIN	TYP.	MAX	UNIT
Reverse (Leakage) Current	IR_{25}	VR= 45 Vdc, Tc= 25°C		300	1000	μA
	IR_{125}	VR= 45 Vdc, Tc= 125°C		100	150	mA
Forward Voltage pulse test, pw= 300 μ s d/c \leq 2%	VF1	IF= 5A, Tc= 25°C		375	475	mV
	VF2	IF= 10A, Tc= 25°C		430	520	mV
	VF3	IF= 20A, Tc= 25°C		510	610	mV
	VF4	IF= 50A, Tc= 25°C		740		mV
	VF5	IF= 10A, Tc= -55°C		480	580	mV
	VF6	IF= 10A, Tc= 125°C		360		mV
Junction Capacitance	Cj1	VR= 10 Vdc		525	600	pF
	Cj2	VR= 5 Vdc		725		pF
Breakdown Voltage	BVR	IR= 1 mA, Tc= 25°C		55		V
		IR= 1 mA, Tc= -55°C	45	50		V